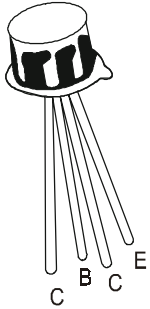


NPN SILICON PLANAR RF TRANSISTOR

BF115



**TO-72
Metal Can Package**

ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)

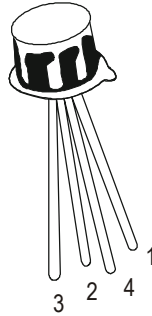
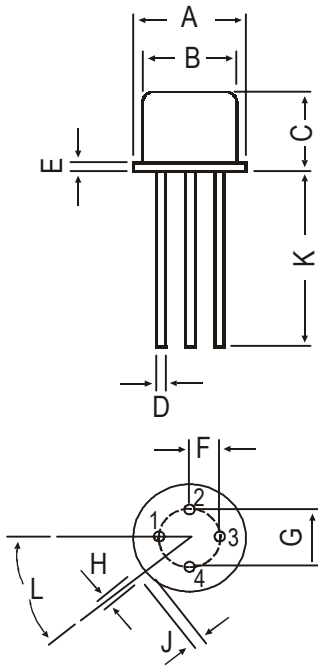
DESCRIPTION	SYMBOL	VALUE	UNIT
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	30	mA
Base Current Continuous	I_B	1	mA
Total Power Dissipation @ Ta=45°C	P_D	145	mW
Operating & Storage Junction Temperature Range	T_j, T_{stg}	-55 to +175	°C
THERMAL RESISTANCE			
Junction to Ambient	$R_{th(j-a)}$	900	°C/W

ELECTRICAL CHARACTERISTICS (Ta=25° C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE			UNIT
			MIN	TYP	MAX	
Collector Emitter Breakdown Voltage	BV_{CEO}^*	$I_C=2mA, I_B=0$	30			V
Collector Base Breakdown Voltage	BV_{CBO}	$I_C=10\mu A, I_E=0$	50			V
Emitter Base Breakdown Voltage	BV_{EBO}	$I_E=10\mu A, I_C=0$	5			V
Collector Cut off Current	I_{CBO}	$V_{CB}=20V, I_E=0, T_a=175^\circ C$		0.5		μA
DC Current Gain	h_{FE}	$I_C=1mA, V_{CE}=10V$	48		167	
		$I_C=20mA^*, V_{CE}=2V$	40			
Base Emitter On Voltage	$V_{BE(on)}$	$I_C=1mA, V_{CE}=10V$	600	700	740	mV
		$I_C=20mA, V_{CE}=2V^*$			1000	mV
DYNAMIC CHARACTERISTICS						
Transition Frequency	f_T	$I_C=1.0mA, V_{CE}=10V, f=100MHz$		230		MHz
Feedback Capacitance	C_{re}	$V_{CB}=10V, I_C=1mA, f=0.45MHz$		0.65	0.8	pF
Noise Figure	NF	$V_{CE}=10V, I_C=1mA, R_g=300K\Omega, f=200KHz$		1.5		dB
		$f=1MHz$		1.2		dB

Pulse Test: pulse Width <300 μ S, Duty Cycle<2%

TO-72 Metal Can Package



PIN CONFIGURATION

- 1. EMITTER
- 2. BASE
- 3. COLLECTOR
- 4. CASE

All dimensions in mm.

DIM	MIN.	MAX.
A	5.24	5.84
B	4.52	4.95
C	4.31	5.33
D	0.40	0.53
E	—	0.76
F	1.14	1.39
G	2.28	2.97
H	0.91	1.17
J	0.71	1.22
K	12.70	—
L	12 DEG	48 DEG

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-72	1 K/Polybag	325 gm/1K pcs	3" x 7.5" x 7.5"	5K	17" x 15" x 13.5"	80K	32 kgs

Disclaimer

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Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.

Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290

e-mail sales@cdil.com www.cdil.com

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